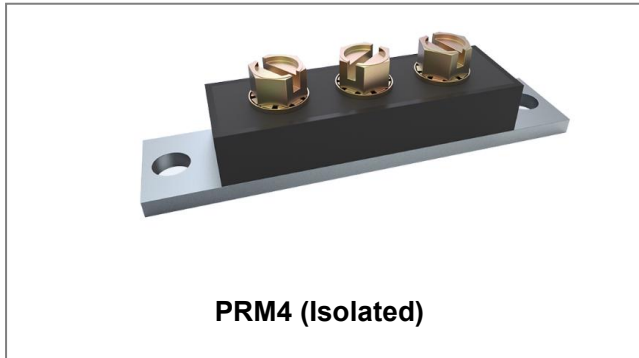


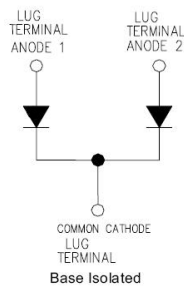
## 306CMQ200 SCHOTTKY RECTIFIER



### Features

- 175°C T<sub>J</sub> operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- High current switching power supply
- Plating power supply
- Free-Wheeling diodes
- Reverse battery protection
- Converters
- UPS System
- Welding

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	200	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> =121°C, rectangular wave form	150(Per Leg)	A
			300(Per Device)	
Peak One Cycle Non-Repetitive Surge Current (Per Leg)	I <sub>FSM</sub>	8.3 ms, half Sine pulse	3840	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 150A, Pulse, T <sub>J</sub> = 25 °C @ 300A, Pulse, T <sub>J</sub> = 25 °C	0.84 -	0.86 1.03	V
	V <sub>F2</sub>	@ 150A, Pulse, T <sub>J</sub> = 125 °C @ 300A, Pulse, T <sub>J</sub> = 125 °C	0.71 -	0.76 0.86	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.0001	10	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	0.8	90	mA
Junction Capacitance(Per leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>sig</sub> = 1MHz	2300	3500	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

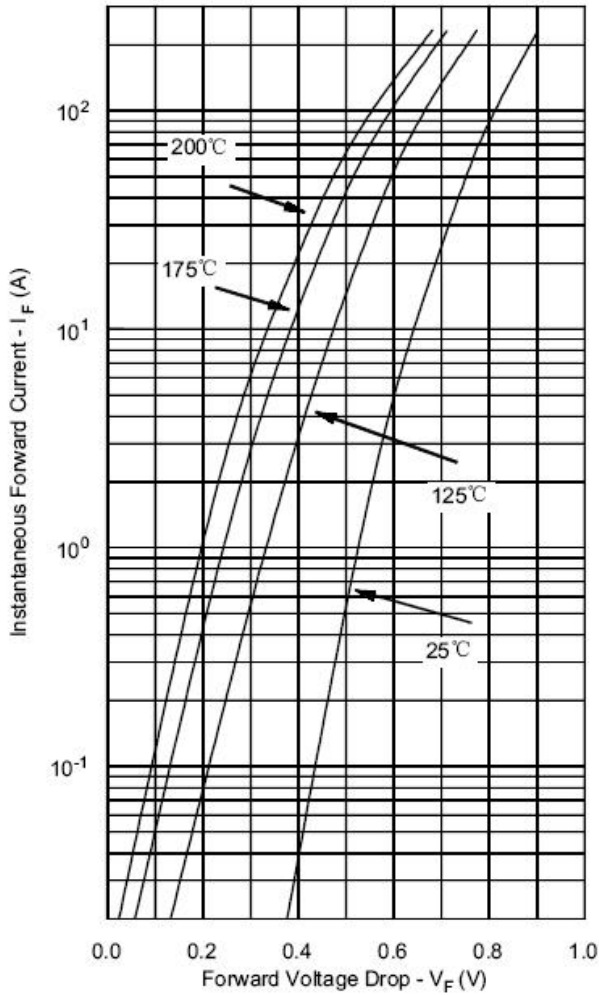
\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

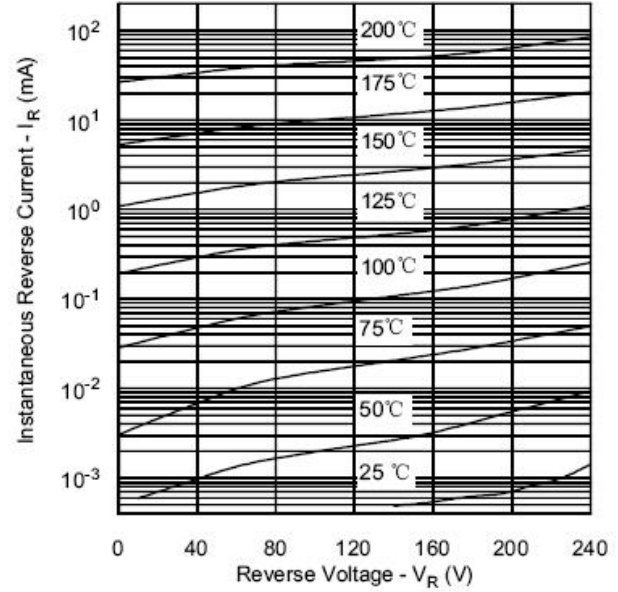
Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	T <sub>J</sub>	-	-55 to +175		°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case(Per leg)	R <sub>θJC</sub>	DC operation	0.50		°C/W
Typical Thermal Resistance Junction to Case(Per package)	R <sub>θJC</sub>	DC operation	0.25		°C/W
Typical Thermal Resistance, case to Heat Sink	R <sub>θcs</sub>	Mounting surface, smooth and greased	0.10		°C/W
Mounting Torque	T <sub>M</sub>	-	Mounting Torque	24(min) 35(max)	Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	79		g
Case Style	PRM4 Isolated				

**Ratings and Characteristics Curves**

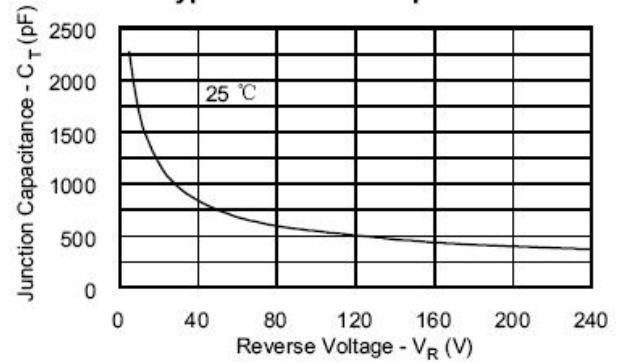
**Typical Forward Characteristics**



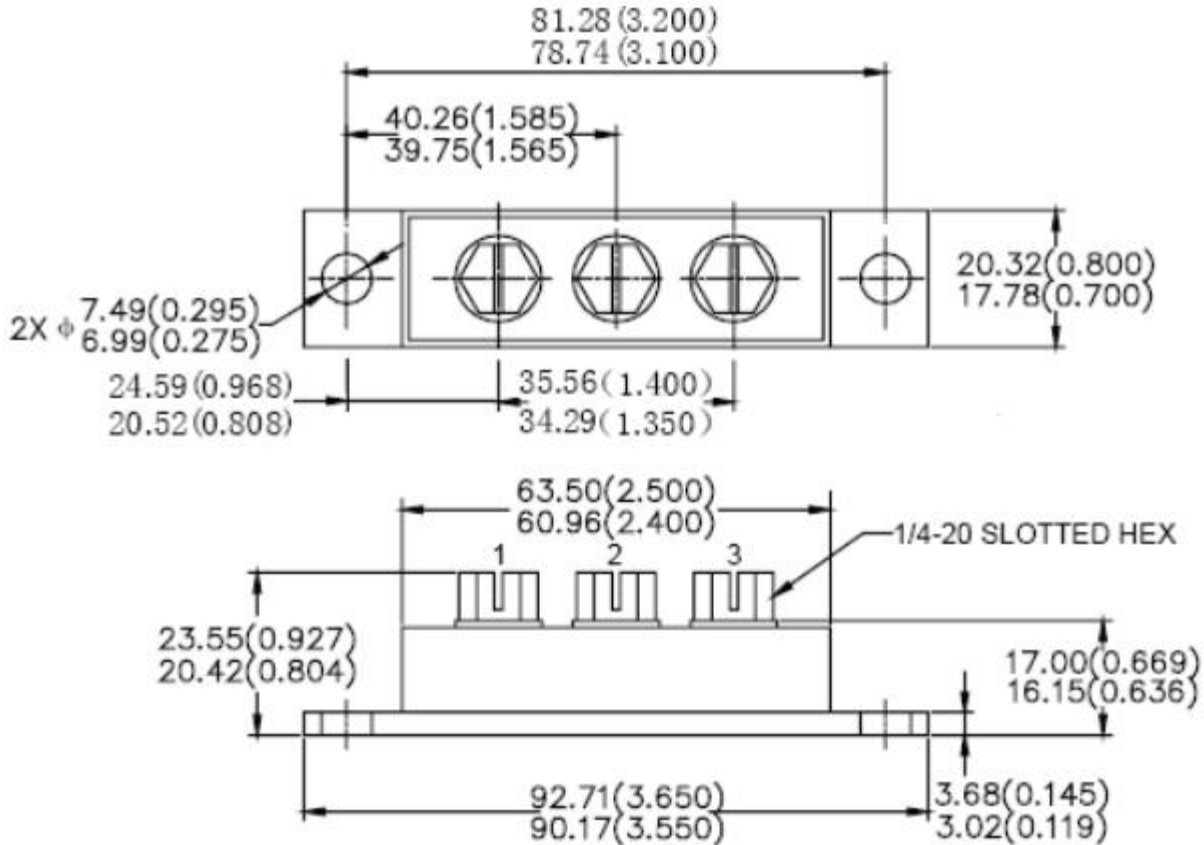
**Typical Reverse Characteristics**



**Typical Junction Capacitance**

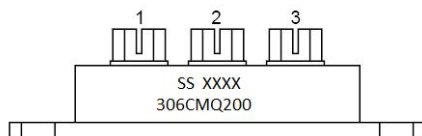


**Mechanical Dimensions PRM4 Isolated (Millimeters/Inches)**



Please Note: Anode 1 = Terminal 1; Anode 2 = Terminal 3; Common Cathode = Terminal 2  
Suffix R Denotes for Reversed Polarity.

**Marking Diagram**



Where XXXX is YYWW

306CMQ200 = Part name  
SS = SS  
YY = Year  
WW = Week

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information**

Device	Package	Shipping
306CMQ200	PRM4 Isolated (Pb-Free)	9 pcs/box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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